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(54) WRITE-IN CIRCUIT FOR NON-VOLATILE ANALOG MEMORY

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PURPOSE: To decrease the time required for write of an analog signal by comparing a threshold voltage of an analog memory with a reference voltage and generating a write-in pulse with a peak value in response to the magnitude of the difference.

CONSTITUTION: When a difference between a threshold voltage of a non-volatile analog memory NVAM and a reference voltage Vs detected at a threshold value detecting circuit 20 becomes greater, a voltage outputted from a voltage control Vx circuit 21 is quickly increased and the peak value of write-in pulse generated from a write-in pulse generating circuit 22 is quickly increased by the increase. As a result, the threshold voltage of the NVAM is rapidly closed to the objective value. On the other hand, when the threshold voltage of the NVAM closes to a desired value and the difference with the voltage Vs becomes smaller, the increment of the write-in pulse is decreased, allowing to adjust the threshold value of the NVAM minutely. When the both are coincident, the circuit 20 gives an inhibiting signal Vy to the circuit 22 to complete the write-in operation.

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